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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

			Group Art Unit	2812;Conf. No. 1562
(Use as ma	ny sheets as neo	cessary)	Examiner Name	
1	of	2	Attorney Docket Number	03108/PHYS00303

Complete if Known

Application Number

First Named Inventor

Filing Date

10/616,873

July 10, 2003

Xunming Deng

			U.	S. PATENT DOCU	UMENTS	
	Cite	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages
Initials No.		NumberKind Code (if known)		MINI-DD-1111		or Relevant Figures Appear
AR		US-	5,082,359	01-1992	Kirkpatrick	
		US-	5,397,737	03-14-1995	Mahan et al.	
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1		US-	6,124,186	09-26-2000	Molenbroek et al.	
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Examiner Initials	Cite No.	Foreign Patent Document  Country Code-Number-Kind Code (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T
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Examiner Signature Date Considered //22/04

(Information Disclosure Statement - FORM/1449A/PTD (PTO/SB/08A)

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Substitute for form 1449B/PTO  INFORMATION DISCLOSURE				Complete if Known  Application Number	10/616,873
				Filing Date	July 10, 2003
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(Use as many sheets as necessary)				Group Art Unit	2812;Conf. No. 1562
				Examiner Name	
Sheet	2	of	2	Attorney Docket Number	03108/PHYS00303

Examiner Cite Initials No. 1		Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			
Ac		H. Povolny, S. Han, X.B., Xiang and X. Deng/Hot-Wire Deposition of c-Si and a-Si Using Different Gas Excitations By A Coiled Filament/Abstract submitted to 19 <sup>th</sup> International Conference Amorphous and Microcrystalline Semiconductors Science and Technology (ICAMS19) Acropolis Center, Nice, France, 27-31 August 2001			
		Xunming Deng/Construction of a novel hot-wire deposition system employing a coiled hot filament/Disclosed at "Amorphous Silicon Team Meeting" for NREL/DOE (Nat'l Renewable Energy Laboratory/Dept. of Energy) in August 2000.			
		S. Yu, E. Gulari, and J. Kanicki/Center for Display Technology and Manufacturing, University of Michigan, Ann Arbor, Michigan 48109/Selective deposition of polycrystalline silicon thin films at low temperature by hot-wire chemical vapor deposition/May 1996.			
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Signature

page 5 of R) (Information Disclosure Statement -- Section 2. FORM 1449A/PTO (PTO/SB/08A)

<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not obtation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>&</sup>lt;sup>1</sup> Unique citation designation number. <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.